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Amendments to the Specification:

Please replace the title with the following amended title:

**METHOD OF FORMING SIDEWALL SPACER USING DUAL-FREQUENCY PLASMA
ENHANCED CVD SILICON NITRIDE FOR SPACER APPLICATION**

Please replace paragraph [0005] with the following amended paragraph:

[0005] For example, by the time the spacers are to be formed to make a semiconductor device, the gate poly conductor is typically patterned. The width of the poly conductor lines would be typically between 300 Å to 800 Å, and height of the poly conductor line is typically in the order of 1000 Å to 2000 Å. Referring to FIG. 1FIG. 2, a substrate 10 is illustrated, having polysilicon lines 20. The deposition thickness of the silicon nitride layer 30 would vary along different regions. The poly conductor (PC) line 20 is the feature over which the spacer needs to be deposited and shaped. Region A of the silicon nitride layer 30 denotes the planar region 31 overlying the substrate 10; region B of the nitride layer 30 denotes the portion overlying the top surface 21 of the PC line ; C denotes the region of the nitride layer 30 covering the vertical side wall 22 of the PC line; region D denotes the transition region of the nitride layer from the vertical sidewall region C to the planar horizontal region A of the nitride layer 30. Typically for a PECVD silicon nitride film, the thickness on vertical sidewall C is about 30 to 80% of the thickness of the planar region A, depending on the aspect ratio. For forming a spacer and using it to define ~~as a~~ device, the transitional region D is of great importance. The transition region D of the nitride layer 30 should be continuous and without seams. The thickness and uniformity of

FIS920040102US1

10710,257

transition region D would vary based on the aspect ratio of the PC line 20. The two big problems for PECVD silicon nitride films for spacer applications is the poor conformality (less than 50%) and the presence of seams 43 (which may be observed from subsequent wet cleans that are used to form cobalt silicide junction contacts to the source-drain regions).

FIS920040102US1